

Application No.: 10/801,884

Docket No.: JCLA12524

**In The Claims:**

Please amend the claims as follows:

**Claims 1-11 (canceled)**

12. (currently amended) A correction pattern for a chemical-mechanical polishing proximity correct, comprising:

a polish area over a wafer, wherein the polish area has a plurality of boundaries and at least a corner;

a protective region set up outside the polish area;

a shadow area set up ~~outside the polish area of the wafer~~ between the polish area and the protection region, wherein the shadow area at least comprises:

a plurality of peripheral sections set up ~~outside~~ along the boundaries of the polish area, wherein the peripheral sections have a first width; and

at least a corner section set up ~~outside~~ along the corner of the polish area, wherein the corner section connects the adjacent peripheral sections, and the corner section has a second width such that the second width is greater than the first width; ~~and~~

~~a protective region set up outside the polish area and the shadow areas of the wafer.~~

13. (original) The correction pattern of claim 12, wherein the peripheral sections have a first width between 1 ~ 20 $\mu$ m.

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14. (original) The correction pattern of claim 12, wherein the corner within the polish area is a straight corner.

15. (original) The correction pattern of claim 14, wherein the second width of the corner shadow area is set according to the following relation:

$$W = A + D = A + (C / \sqrt{2}) = A + (B / 2)$$

where W is the second width,

A is the first width, wherein the first width is between 1 ~ 20 $\mu$ m,

C is the shortest distance between a line joining the end points of the outer edges of two neighboring peripheral shadow areas and the corner of the polish area,

B is the distance from a cross point between the aforementioned line and the boundary of the polish area to the corner, wherein B is between 0.5 ~ 5 $\mu$ m, and

D is the difference between the second width and the first width.

16. (original) The correction pattern of claim 12, wherein the polish area further comprises at least a device structure set up on the wafer.

17. (original) The correction pattern of claim 16, wherein the polish area further comprises a material layer formed over the device structure.

18. (original) The correction pattern of claim 17, wherein the protected area further comprises a protective layer formed over the material layer.